

47QM8205V-VB Datasheet

Dual N-Channel MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$V_{DS}(V)$ $R_{DS(on)}(\Omega)$			
20	0.024 at V _{GS} = 4.5 V	6.0		
	0.028 at V _{GS} = 2.5 V	5.0		

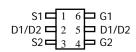
FEATURES

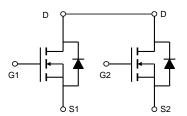
- Halogen-free Option Available
- Trench Power MOSFETs 100 % $\rm R_{\rm g}$ Tested
- Compliant to RoHS Directive 2002/95/EC



COMPLIANT

TSOP6 **Top View**





ABSOLUTE MAXIMUM RATINGS T	T _A = 25 °C, unles	s otherwise n	oted			
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	20		V	
Gate-Source Voltage		V_{GS}	± 12			
Continuous Dusin Courset /T 450 90\8	T _A = 25 °C	- I _D	6.0	5.2		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		4.8	4.2	٨	
Pulsed Drain Current		I _{DM}	30		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	1.5	1.0		
Mariana Barra Biraira da	T _A = 25 °C	Б	1.5	1.0	W	
Maximum Power Dissipation ^a	T _A = 70 °C	P _D	0.96	0.64	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Тур.	Max.	Unit		
Mariana haria ta Arkinda	t ≤ 10 s	R _{thJA}	72	83	°C/W	
Maximum Junction-to-Ambient ^a	Steady State	'`thJA	100	120		
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	55	70		

a. Surface Mounted on FR4 board, $t \le 10 \text{ s.}$

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply.



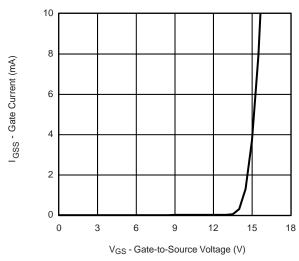
SPECIFICATIONS T _J = 25 °C, unless otherwise noted									
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit			
Static									
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.5		1.5	V			
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 200	nA			
Zana Cata Malta na Busin Commant		V _{DS} = 20 V, V _{GS} = 0 V		1					
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V, T _J = 70 °C			25	μA			
On-State Drain Current ^b	I _{D(on)}	$V_{DS} \le 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			Α			
5 1 0 0 0 1 1 b	В	$V_{GS} = 4.5 \text{ V}, I_D = 5.5 \text{ A}$		0.024		Ω			
Drain-Source On-State Resistance ^b	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 3.5 \text{ A}$		0.028					
Forward Transconductance ^b	9 _{fs}	V _{DS} = 10 V, I _D = 5.5 A		30		S			
Diode Forward Voltage ^b	V_{SD}	$I_S = 1.5 \text{ A}, V_{GS} = 0 \text{ V}$		0.71	1.2	V			
Dynamic ^a									
Total Gate Charge	Qg			12	18				
Gate-Source Charge	Q_{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 5.5 \text{ A}$		2.2		nC			
Gate-Drain Charge	Q_{gd}			3.6					
Turn-On Delay Time	t _{d(on)}			245	365				
Rise Time	t _r	V_{DD} = 10 V, R_L = 10 Ω		330	495	200			
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1 A, V_{GEN} = 4.5 V, R_G = 6 Ω		860	1300	ns			
Fall Time	t _f			510	765				

Notes:

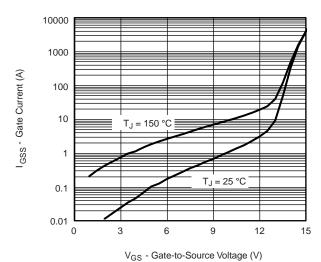
- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



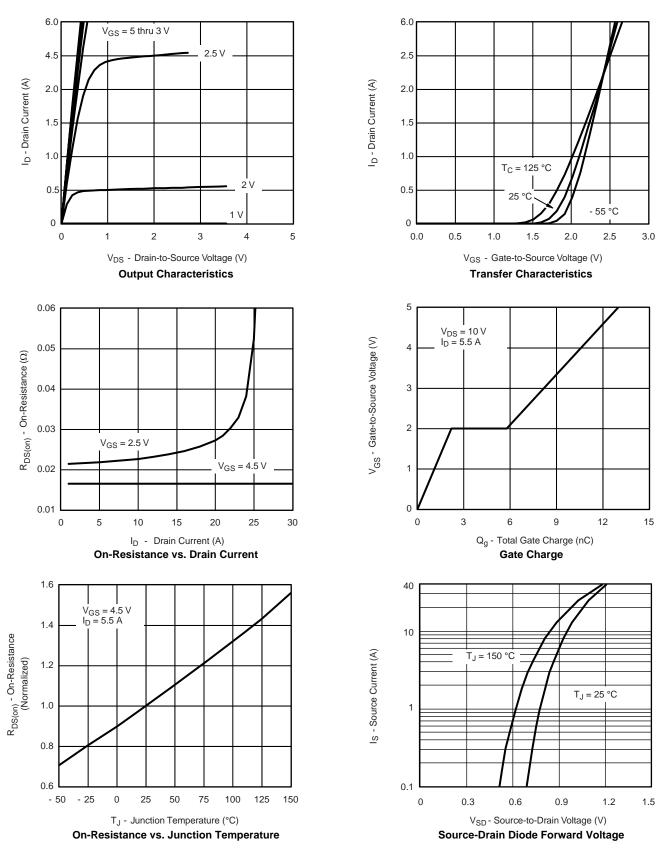
Gate-Current vs. Gate-Source Voltage



Gate Current vs. Gate-Source Voltage

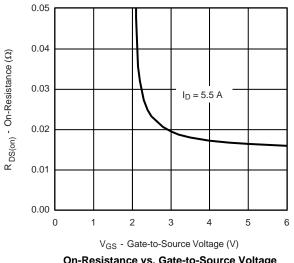


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

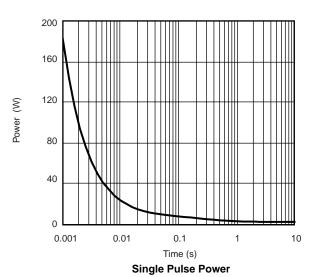




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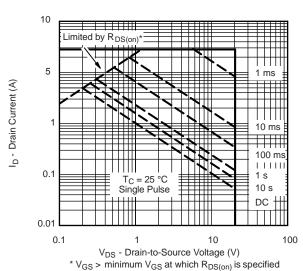


On-Resistance vs. Gate-to-Source Voltage

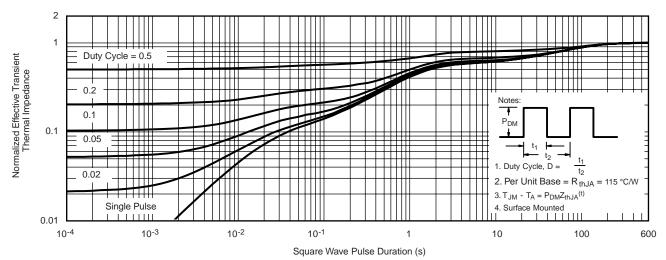


0.4 I_D = 250 μA 0.2 V_{GS(th)} Variance (V) 0.0 - 0.2 - 0.4 - 0.6 0 - 50 - 25 25 50 75 100 125 150 T_J - Temperature (°C)

Threshold Voltage



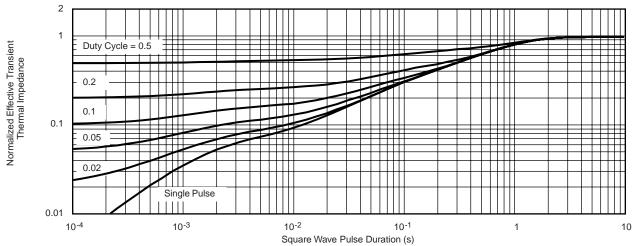
Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

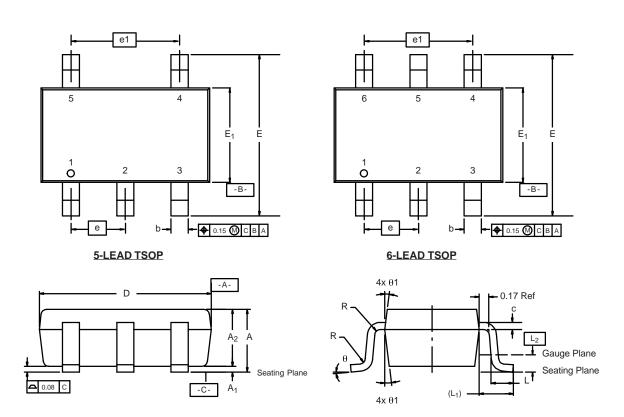


Normalized Thermal Transient Impedance, Junction-to-Foot



TSOP: 5/6-LEAD

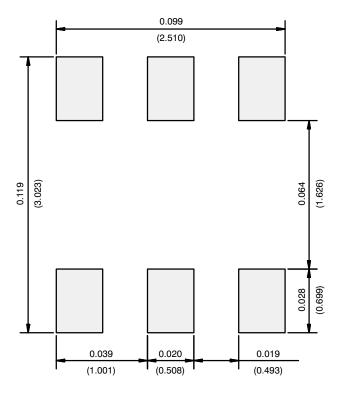
JEDEC Part Number: MO-193C



	MILLIMETERS			INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A ₁	0.01	-	0.10	0.0004	-	0.004	
A ₂	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
Е	2.70	2.85	2.98	0.106	0.112	0.117	
E ₁	1.55	1.65	1.70	0.061	0.065	0.067	
е	0.95 BSC			0.0374 BSC			
e ₁	1.80	1.90	2.00	0.071	0.075	0.079	
L	0.32	-	0.50	0.012	-	0.020	
L ₁	0.60 Ref			0.024 Ref			
L ₂	0.25 BSC			0.010 BSC			
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
θ_1	7° Nom			7° Nom			
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							



RECOMMENDED MINIMUM PADS FOR TSOP-6



Recommended Minimum Pads Dimensions in Inches/(mm)



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